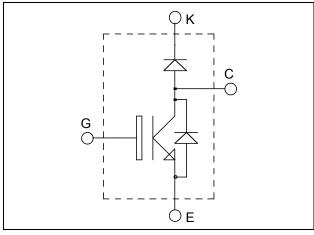
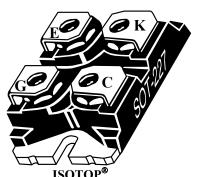
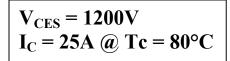


ISOTOP® Boost chopper Trench + Field Stop fast IGBT4 Power module







### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

#### **Features**

- Trench + Field Stop Fast IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Low leakage current
  - RBSOA and SCSOA rated

### • Boost SiC Schottky Diode

- Zero reverse recovery
- Zero forward recovery
- Temperature Independent switching behavior
- Positive temperature coefficient on VF
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

### **Benefits**

- Low conduction losses
- Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- ullet Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

### All ratings @ $T_i = 25$ °C unless otherwise specified

### Absolute maximum ratings

| Symbol      | Parameter                             |                      | Max ratings | Unit |
|-------------|---------------------------------------|----------------------|-------------|------|
| $V_{CES}$   | Collector - Emitter Breakdown Voltage |                      | 1200        | V    |
| T           | Continuous Collector Current          | $T_C = 25^{\circ}C$  | 45          |      |
| $I_{C}$     | $T_{\rm C} = 80$                      | $T_C = 80$ °C        | 25          | Α    |
| $I_{CM}$    | Pulsed Collector Current              | $T_C = 25^{\circ}C$  | 50          |      |
| $ m V_{GE}$ | Gate – Emitter Voltage                |                      | ±20         | V    |
| $P_{D}$     | Maximum Power Dissipation             | $T_C = 25^{\circ}C$  | 170         | W    |
| RBSOA       | Reverse Bias Safe Operating Area      | $T_j = 150^{\circ}C$ | 50A @ 1100V |      |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

1 - 5



### **Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                        |                     | Min | Typ  | Max | Unit |
|---------------|--------------------------------------|--|---------------------|-----|------|-----|------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 1200V$          |                     |     |      | 250 | μΑ   |
| V             | Collector Emitter saturation Voltage | $V_{GE} = 15V$                         | $T_j = 25^{\circ}C$ | 1.7 | 2.05 | 2.4 | V    |
| $V_{CE(sat)}$ |                                      | $I_C = 25A$ $T_j = 150$ °C             |                     | 2.6 |      | ·   |      |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 0.8 \text{mA}$ |                     | 5.0 | 5.8  | 6.5 | V    |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V$ , $V_{CE} = 0V$         |                     |     |      | 400 | nA   |

**Dynamic Characteristics** 

| ·                   | Characteristic               | Test Conditions   |   | Min                 | Typ  | Max | Unit |    |
|---------------------|------------------------------|---|---|---------------------|------|-----|------|----|
| Cies                | Input Capacitance            | $V_{GE} = 0V$ $V_{CE} = 25V$  |   |                     | 1430 |     |      |    |
| Coes                | Output Capacitance           |   |   |                     | 115  |     | pF   |    |
| $C_{res}$           | Reverse Transfer Capacitance | f = 1MHz  | f = 1MHz  |                     | 85   |     |      |    |
| $Q_{G}$             | Gate charge                  | $V_{GE} = \pm 15V ; V_{CE} = 600V$<br>$I_{C} = 25A$                                   |   |                     | 0.2  |     | μС   |    |
| $T_{d(on)}$         | Turn-on Delay Time           |   | Inductive Switching (25°C)<br>$V_{GE} = \pm 15V$<br>$V_{CE} = 600V$ |                     | 130  |     | ns   |    |
| $T_{\rm r}$         | Rise Time                    |   |   |                     | 20   |     |      |    |
| T <sub>d(off)</sub> | Turn-off Delay Time          | $I_{\rm CE} = 600  \text{V}$<br>$I_{\rm C} = 25  \text{A}$                            |   |                     | 300  |     |      |    |
| $T_{\rm f}$         | Fall Time                    | $R_G = 20\Omega$  |   |                     | 45   |     |      |    |
| $T_{d(on)}$         | Turn-on Delay Time           | Inductive Switching (150°C)<br>$V_{GE} = \pm 15V$<br>$V_{CE} = 600V$<br>$I_{C} = 25A$ |   |                     | 150  |     | ns   |    |
| T <sub>r</sub>      | Rise Time                    |   |   |                     | 35   |     |      |    |
| T <sub>d(off)</sub> | Turn-off Delay Time          |   |   |                     | 350  |     |      |    |
| $T_{\mathbf{f}}$    | Fall Time                    | $R_G = 20\Omega$  | ~   |                     | 80   |     |      |    |
| Eon                 | Turn-on Switching Energy     | $V_{GE} = \pm 15V$  | $T_J = 25^{\circ}C$   |                     | 1.2  |     | mJ   |    |
| Lon                 |                              |   | $T_J = 150$ °C  |                     | 1.8  |     | 1113 |    |
| $E_{\text{off}}$    | Turn-off Switching Energy    | $I_C = 25A$ $R_G = 20\Omega$  | -, -,   | $T_J = 25^{\circ}C$ |      | 1.5 |      | mJ |
| Loff                | Turn-on Switching Energy     |   | $T_{\rm J} = 150^{\circ}{\rm C}$                                    |                     | 2.2  |     | 1113 |    |
| $I_{sc}$            | Short Circuit data           | $V_{GE} \le 15V ; V_{Bus} = 900V$<br>$t_p \le 10 \mu s ; T_j = 150^{\circ} C$         |   |                     | 100  |     | A    |    |

## Chopper SiC diode ratings and characteristics

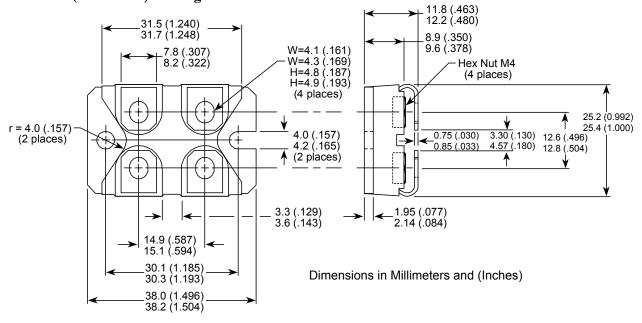
| Symbol                | Characteristic                          | Test Conditions                                  |                        | Min  | Typ | Max | Unit |
|-----------------------|---|--|------------------------|------|-----|-----|------|
| $V_{RRM}$             | Maximum Peak Repetitive Reverse Voltage |  |                        | 1200 |     |     | V    |
| Ţ                     | Maximum Reverse Leakage Current         | V <sub>R</sub> =1200V                            | $T_j = 25^{\circ}C$    |      | 70  | 500 | ^    |
| $I_{RM}$              |   |  | $T_{j} = 175^{\circ}C$ |      | 200 | 700 | μΑ   |
| $I_F$                 | DC Forward Current                      |  | Tc = 125°C             |      | 15  |     | Α    |
| $V_{\mathrm{F}}$      | Diede Ferward Voltage                   | viode Forward Voltage $I_F = 15A$                | $T_i = 25^{\circ}C$    |      | 1.5 | 1.8 | V    |
| <b>v</b> <sub>F</sub> | Diode Forward Voltage                   |  | $T_{i} = 175^{\circ}C$ |      | 2.2 | 3   | V    |
| Qc                    | Total Capacitive Charge                 | $I_F = 15A, V_R = 600V$<br>di/dt = 400A/\mus     |                        |      | 100 |     | nC   |
| С                     | Total Capacitance                       | $f = 1MHz, V_R = 400V$<br>$f = 1MHz, V_R = 800V$ |                        |      | 74  |     | рF   |
|                       |   |  |                        |      | 54  |     | pr   |



### Thermal and package characteristics

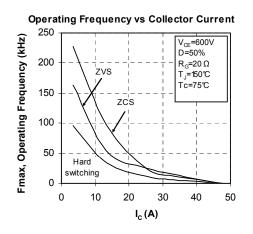
| Symbol           | Characteristic   |           | Min  | Тур  | Max | Unit |
|------------------|--|-----------|------|------|-----|------|
| $R_{thJC}$       | Junction to Case Thermal Resistance  | IGBT      |      |      | 0.9 | °C/W |
|                  |  | SiC Diode |      |      | 1.1 |      |
| $R_{thJA}$       | Junction to Ambient (IGBT & Diode)   |           |      |      | 20  |      |
| $V_{ISOL}$       | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz                |           | 2500 |      |     | V    |
| $T_{J}, T_{STG}$ | Storage Temperature Range  |           | -55  |      | 175 | °C   |
| $T_{ m L}$       | fax Lead Temp for Soldering:0.063" from case for 10 sec 300                  |           | C    |      |     |      |
| Torque           | Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine) |           |      |      | 1.5 | N.m  |
| Wt               | Package Weight   |           |      | 29.2 |     | g    |

## **SOT-227 (ISOTOP®) Package Outline**

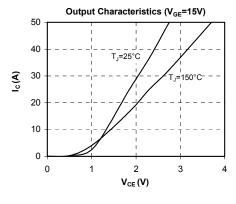


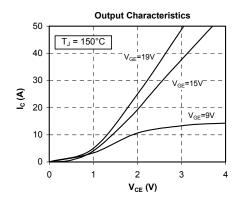
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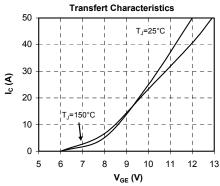
### **Typical Performance Curve**

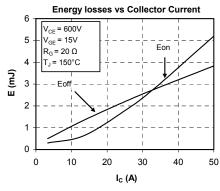


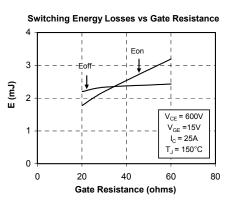


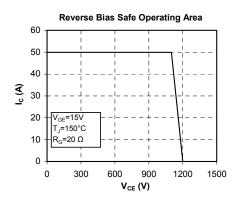


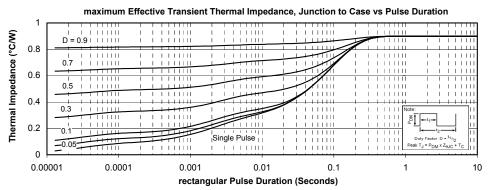












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